

FEATURES

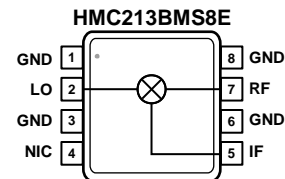
Passive: no dc bias required
Conversion loss: 10 dB typical
Input IP3: 21 dBm typical
RoHS compliant, ultraminiature package: 8-lead MSOP

APPLICATIONS

Base stations
**Personal Computer Memory Card International Association
(PCMCIA) transceivers**
Wireless local loops

GENERAL DESCRIPTION

The HMC213BMS8E is an ultraminiature double balanced mixer in a plastic, 8-lead mini small outline package (MSOP). This passive monolithic microwave integrated circuit (MMIC) mixer is constructed of gallium arsenide (GaAs) Schottky diodes and novel planar transformer baluns on the chip. The

FUNCTIONAL BLOCK DIAGRAM

NOTES
1. NIC = NOT INTERNALLY CONNECTED. THESE PINS CAN BE CONNECTED TO RF/DC GROUND. PERFORMANCE IS NOT AFFECTED.

16435-001

Figure 1.

device can be used as an upconverter, downconverter, biphas demodulator or modulator, or phase comparator. The consistent MMIC performance improves system operation and ensures regulatory compliance.

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REVISION HISTORY

2/2018—Revision 0: Initial Version

SPECIFICATIONS

Ambient temperature (T_A) = 25°C, IF = 100 MHz, LO = 13 dBm, upper sideband. All measurements performed as a downconverter on the evaluation printed circuit board (PCB), unless otherwise noted.

Table 1.

| Parameter | Symbol | Min | Typ | Max | Unit | Test Conditions/Comments |
|--------------------------------|------------|-----|------|-----|------|--------------------------|
| FREQUENCY RANGE | | | | | | |
| RF | RF | 1.5 | | 4.5 | GHz | |
| LO Input | LO | 1.5 | | 4.5 | GHz | |
| IF | IF | DC | | 1.5 | GHz | |
| LO AMPLITUDE | | | | | | |
| | | 9 | 13 | 15 | dBm | |
| 1.5 GHz TO 4.5 GHz PERFORMANCE | | | | | | |
| Downconverter | IF_{OUT} | | | | | LO = 13 dBm |
| Conversion Loss | | | 10 | 11 | dB | |
| Input Third-Order Intercept | IP3 | 16 | 21 | | dBm | |
| Input 1 dB Compression Point | P1dB | | 11 | | dBm | |
| Upconverter | IF_{IN} | | | | | $IF_{IN} = 100$ MHz |
| Conversion Loss | | | 10 | | dB | |
| Input Third-Order Intercept | IP3 | | 17 | | dBm | |
| Input 1 dB Compression Point | P1dB | | 8 | | dBm | |
| Isolation | | | | | | |
| RF to IF | | 8 | 13 | | dB | |
| LO to RF | | 27 | 32 | | dB | |
| LO to IF | | 23 | 30 | | dB | |
| 1.7 GHz TO 3.6 GHz PERFORMANCE | | | | | | |
| Downconverter | IF_{OUT} | | | | | LO = 10 dBm |
| Conversion Loss | | | 10.5 | | dB | |
| Input Third-Order Intercept | IP3 | | 19 | | dBm | |
| Input 1 dB Compression Point | P1dB | | 10.5 | | dBm | |
| Upconverter | IF_{IN} | | | | | $IF_{IN} = 100$ MHz |
| Conversion Loss | | | 9 | | dB | |
| Input Third-Order Intercept | IP3 | | 12 | | dBm | |
| Input 1 dB Compression Point | P1dB | | 6 | | dBm | |
| Isolation | | | | | | |
| RF to IF | | | 13 | | dB | |
| LO to RF | | | 31 | | dB | |
| LO to IF | | | 27 | | dB | |

ABSOLUTE MAXIMUM RATINGS

Table 2.

| Parameter | Rating |
|---|-----------------|
| RF Input Power | 13 dBm |
| LO Input Power | 27 dBm |
| IF Input Power | 13 dBm |
| IF Source/Sink Current | 9 mA |
| Reflow Temperature | 260°C |
| Continuous Power Dissipation, P_{DISS} ($T_A = 85^\circ\text{C}$, Derate 15.9 mW/ $^\circ\text{C}$ Above 85°C) | 1.424 W |
| Maximum Junction Temperature | 175°C |
| Operating Temperature Range | -40°C to +85°C |
| Storage Temperature Range | -65°C to +150°C |
| Lead Temperature Range | -65°C to +150°C |
| Electrostatic Discharge (ESD) Sensitivity | |
| Human Body Model | 2000 V |
| Field Induced Charged Device Model | 1250 V |

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

Thermal performance is directly linked to PCB design and operating environment. Careful attention to PCB thermal design is required.

θ_{JA} is the natural convection junction to ambient thermal resistance measured in a one cubic foot sealed enclosure. θ_{JC} is the junction to case thermal resistance.

Table 3. Thermal Resistance

| Package Type | θ_{JA} | θ_{JC} | Unit |
|-------------------|---------------|---------------|---------------------------|
| RM-8 ¹ | 165.6 | 63 | $^\circ\text{C}/\text{W}$ |

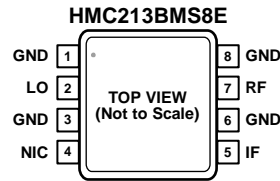
¹ See JEDEC standard JESD51-2 for additional information on optimizing the thermal impedance (PCB with 3 × 3 vias).

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



NOTES
 1. NIC = NOT INTERNALLY CONNECTED. THESE PINS CAN BE CONNECTED TO RF/DC GROUND. PERFORMANCE IS NOT AFFECTED.

Figure 2. Pin Configuration

Table 4. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
|------------|----------|--|
| 1, 3, 6, 8 | GND | Ground. Connect these pins to RF/dc ground. |
| 2 | LO | Local Oscillator (LO) Port. This pin is ac-coupled and matched to 50 Ω. |
| 4 | NIC | Not Internally Connected. These pins can be connected to RF/dc ground. Performance is not affected. |
| 5 | IF | Intermediate Frequency (IF) Port. This pin is dc-coupled. For applications not requiring operation to dc, dc block this port externally using a series capacitor of a value chosen to pass the necessary IF frequency range. For operation to dc, this pin must not source or sink more than 9 mA of current or die malfunction and possible die failure can result. See Figure 5 for the interface schematic. |
| 7 | RF | Radio Frequency (RF) Port. This pin is ac-coupled and matched to 50 Ω. |

INTERFACE SCHEMATICS



Figure 3. GND Interface Schematic

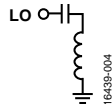


Figure 4. LO Interface Schematic

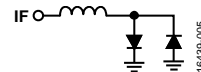


Figure 5. IF Interface Schematic

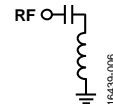


Figure 6. RF Interface Schematic

TYPICAL PERFORMANCE CHARACTERISTICS

DOWNCONVERTER PERFORMANCE

$I_{F_{OUT}} = 100 \text{ MHz}$, Upper Sideband

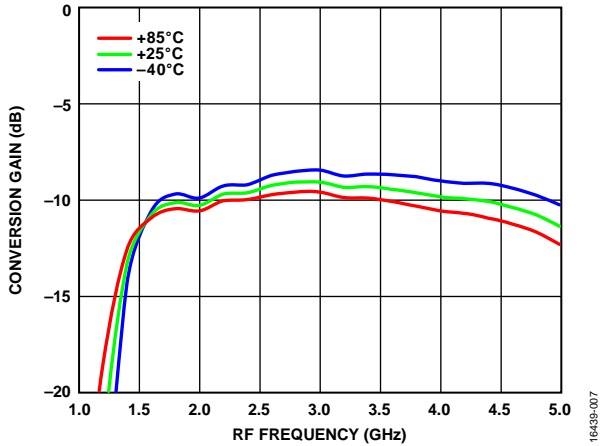


Figure 7. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

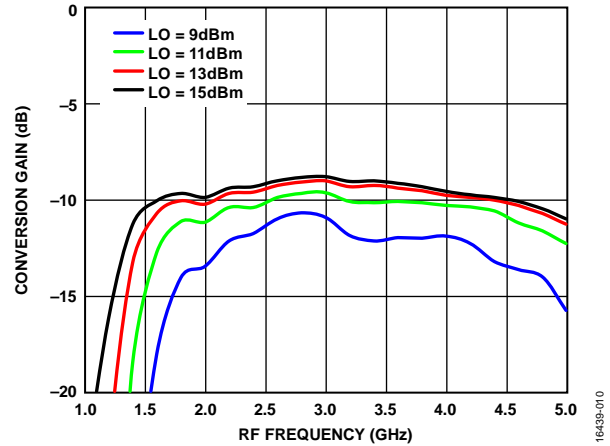


Figure 10. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

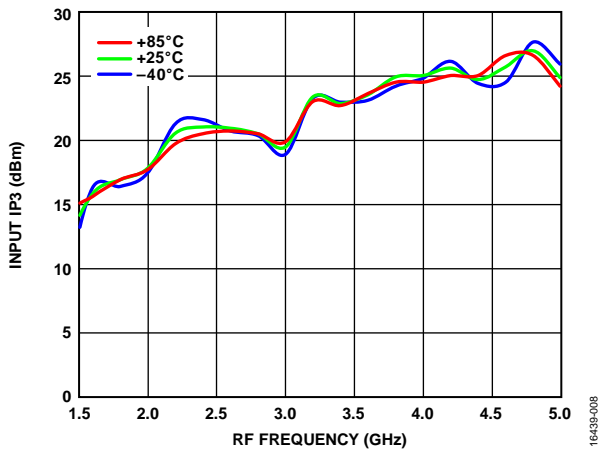


Figure 8. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

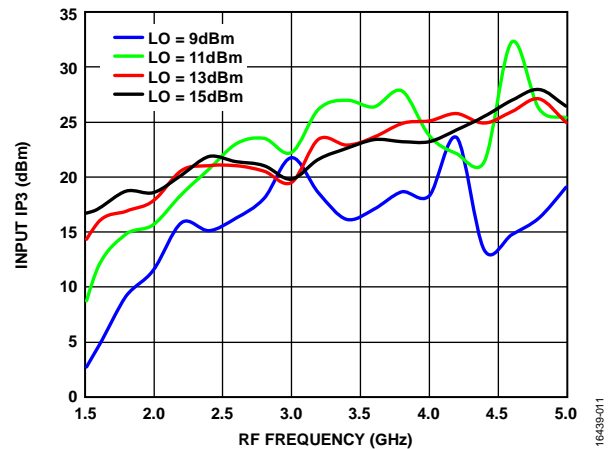


Figure 11. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

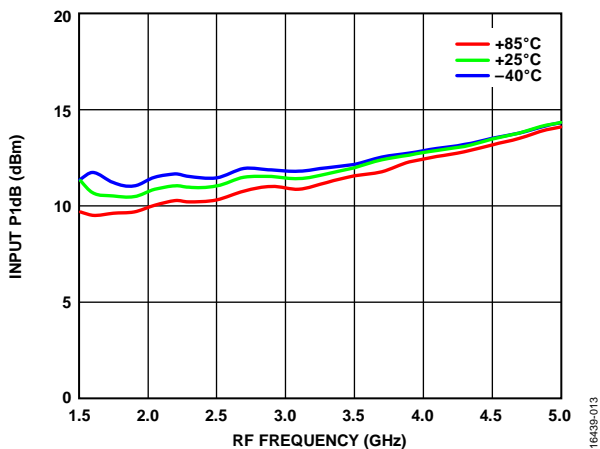


Figure 9. Input P1dB vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

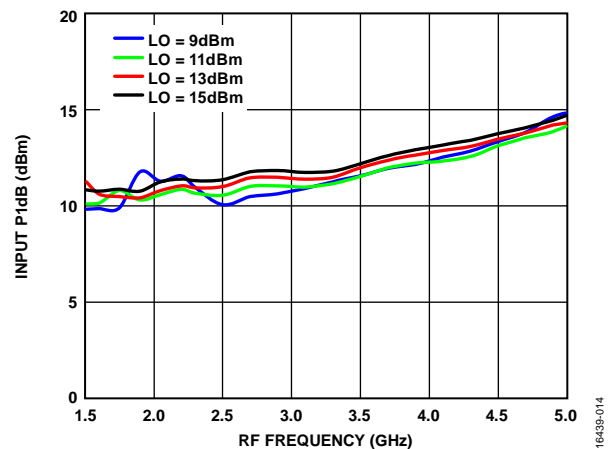


Figure 12. Input P1dB vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

$IF_{OUT} = 100 \text{ MHz, Lower Sideband}$

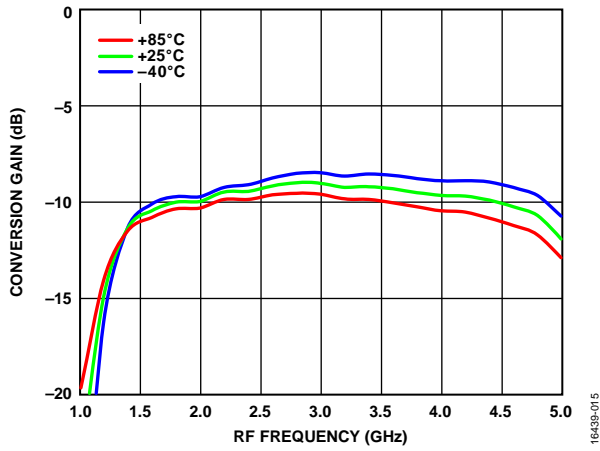


Figure 13. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

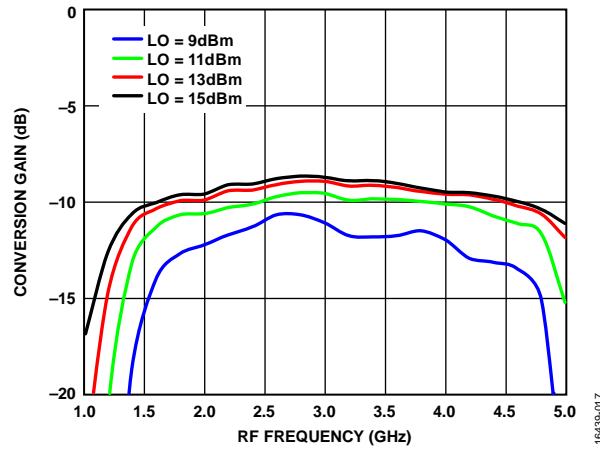


Figure 15. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

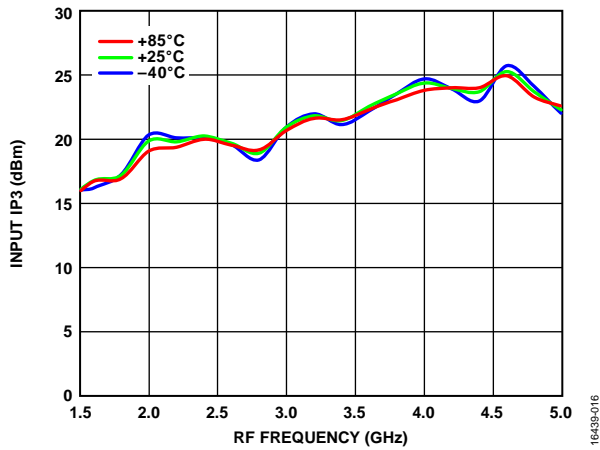


Figure 14. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

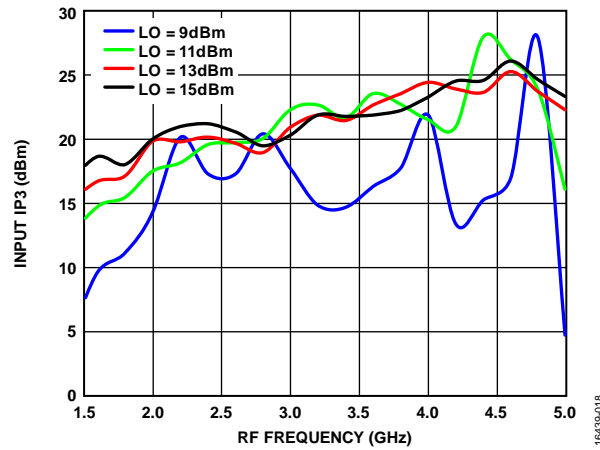


Figure 16. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

$IF_{OUT} = 1500\text{ MHz}$, Upper Sideband

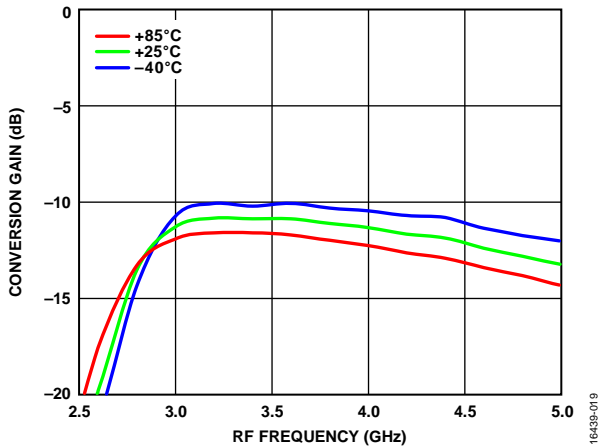


Figure 17. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13\text{ dBm}$

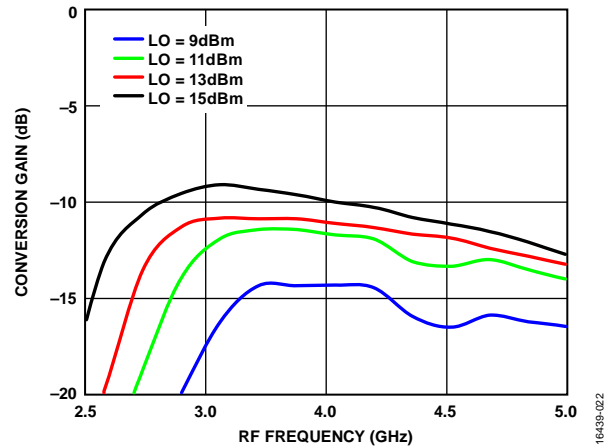


Figure 20. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

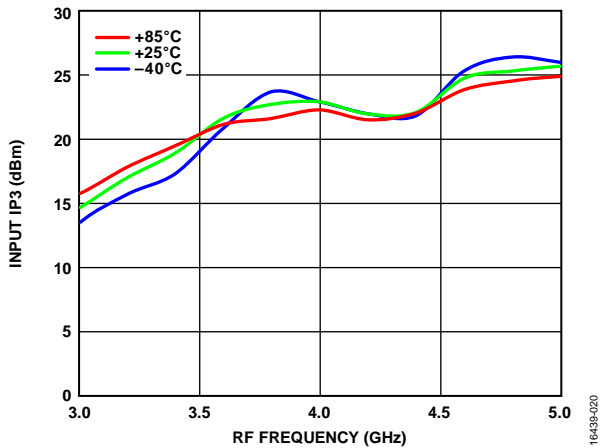


Figure 18. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13\text{ dBm}$

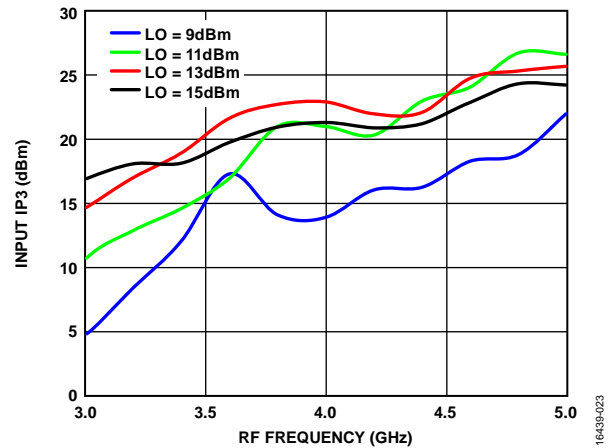


Figure 21. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

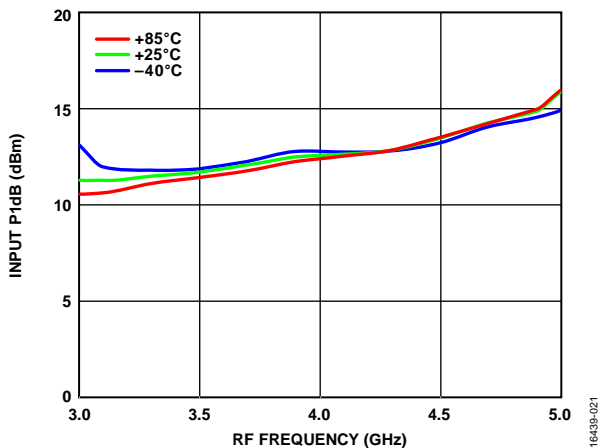


Figure 19. Input P1dB vs. RF Frequency at Various Temperatures, $LO = 13\text{ dBm}$

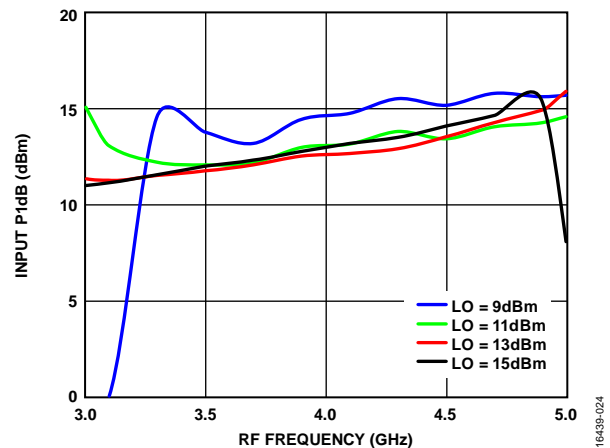


Figure 22. Input P1dB vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

$IF_{OUT} = 1500 \text{ MHz}$, Lower Sideband

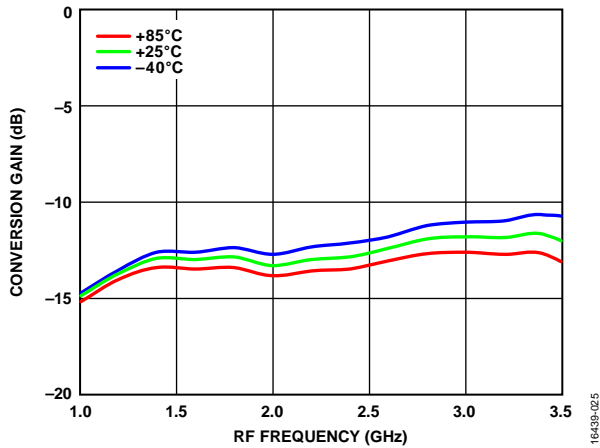


Figure 23. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

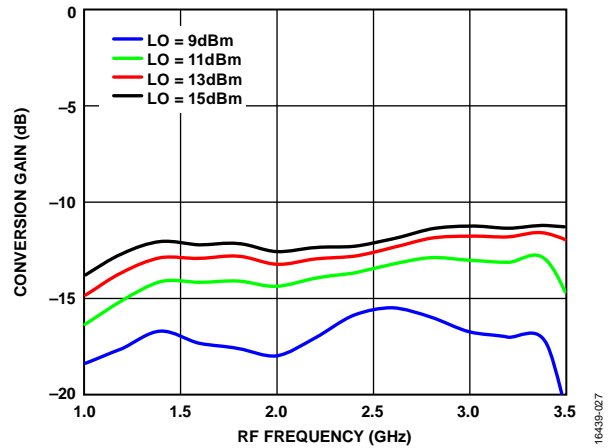


Figure 25. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

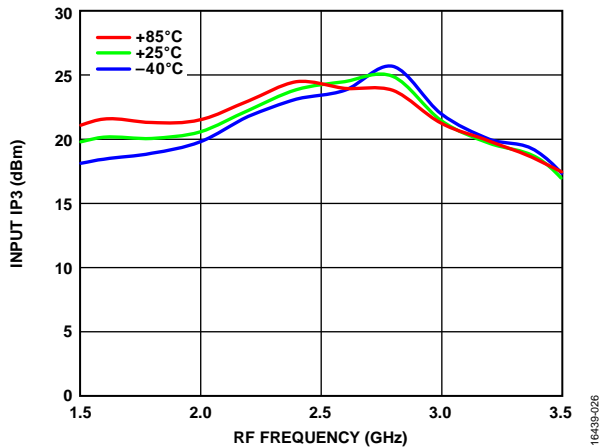


Figure 24. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

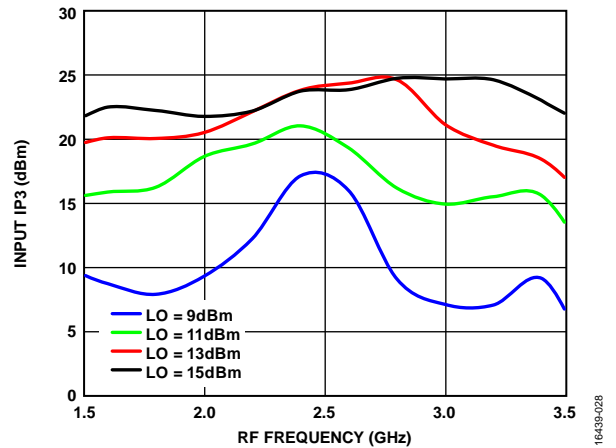


Figure 26. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

UPCONVERTER PERFORMANCE

$IF_{IN} = 100 \text{ MHz}$, Upper Sideband

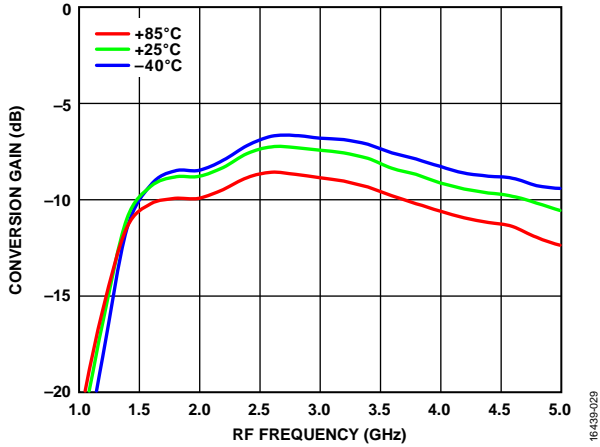


Figure 27. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

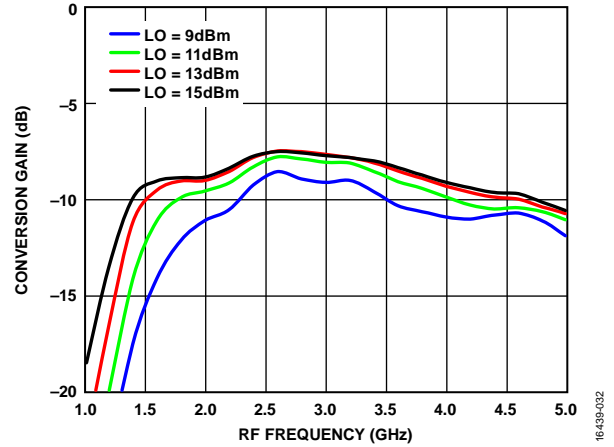


Figure 30. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

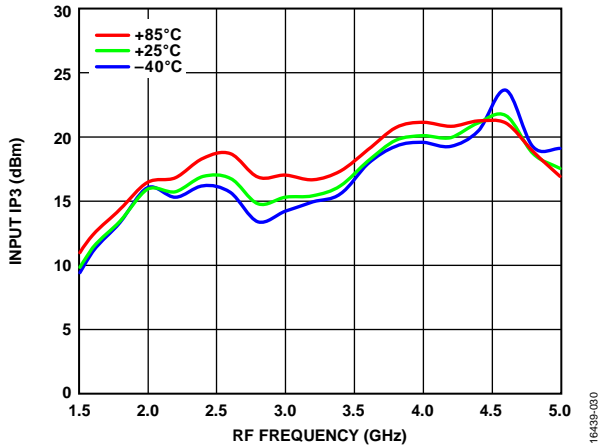


Figure 28. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

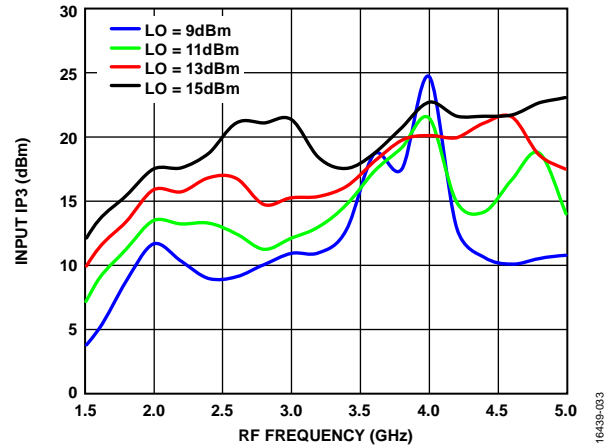


Figure 31. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

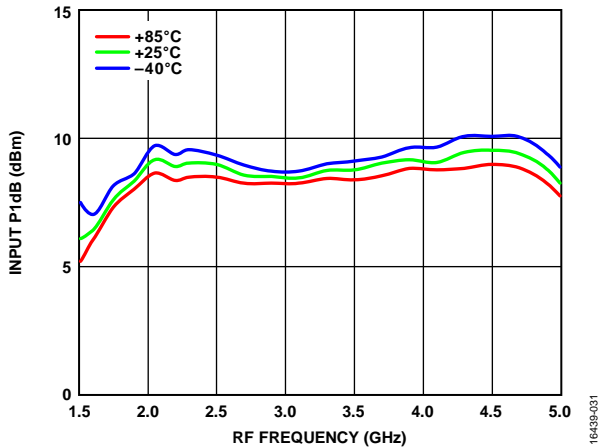


Figure 29. Input P1dB vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

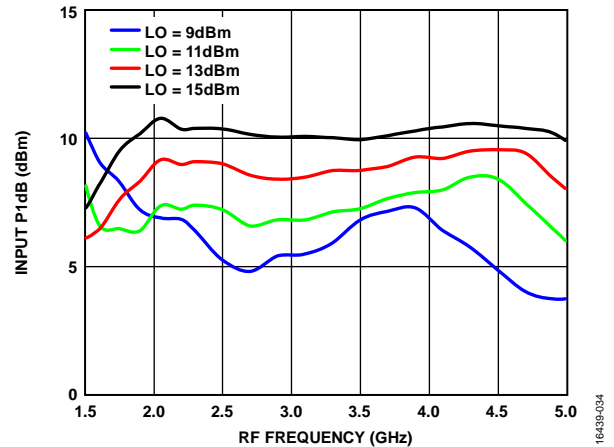


Figure 32. Input P1dB vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

$IF_{IN} = 100 \text{ MHz}$, Lower Sideband

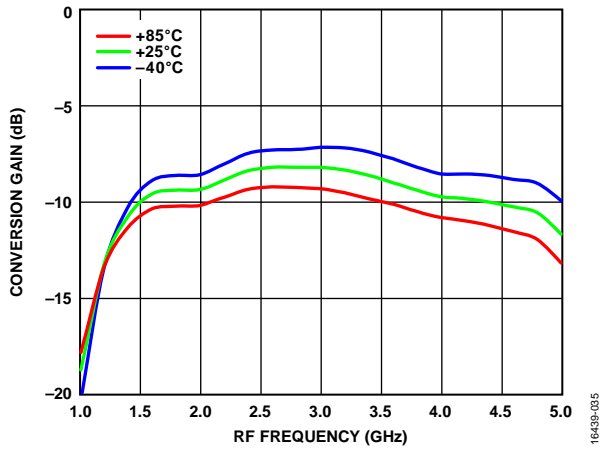


Figure 33. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

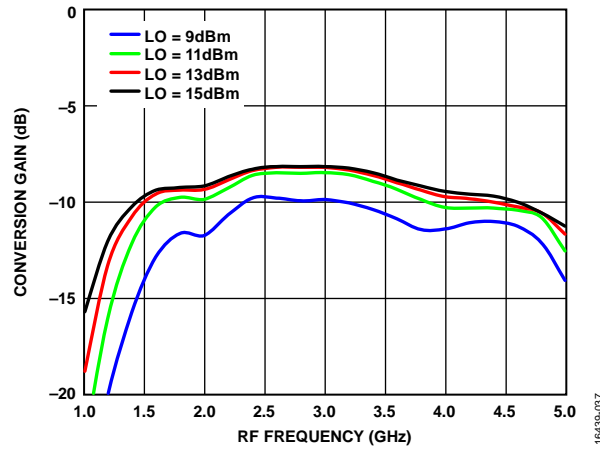


Figure 35. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

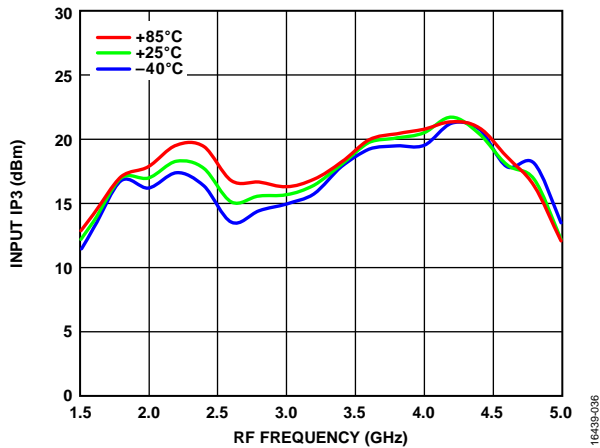


Figure 34. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

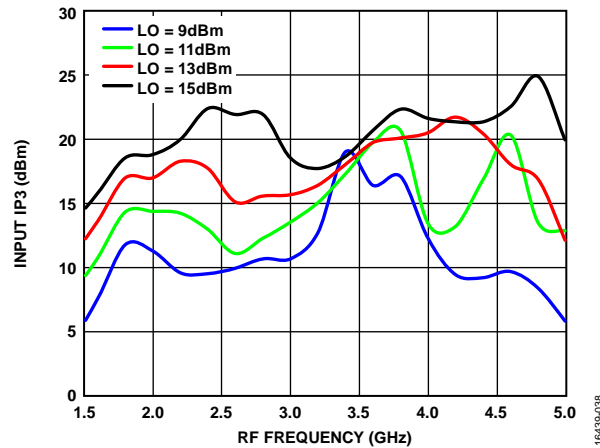


Figure 36. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

$IF_{IN} = 1500 \text{ MHz}$, Upper Sideband

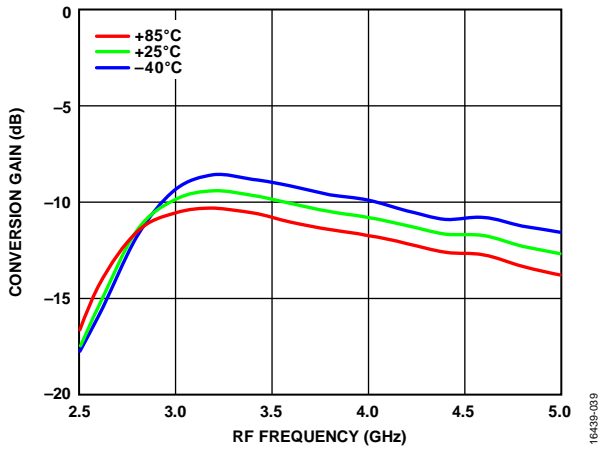


Figure 37. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

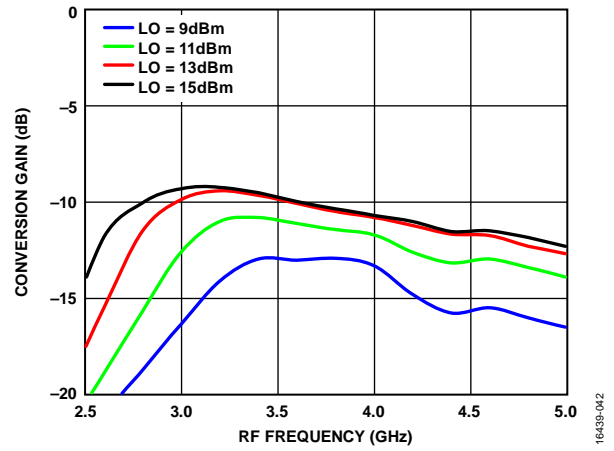


Figure 40. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

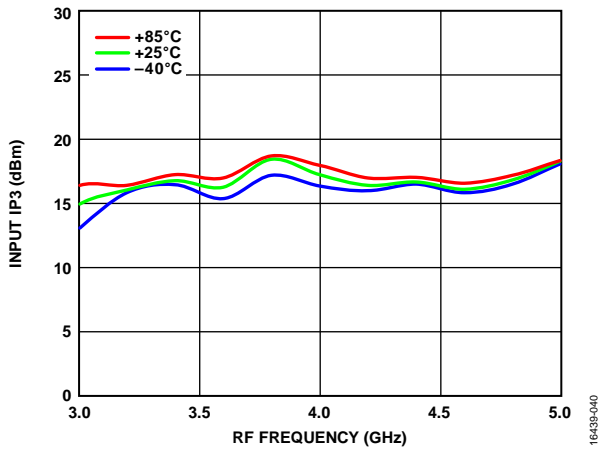


Figure 38. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

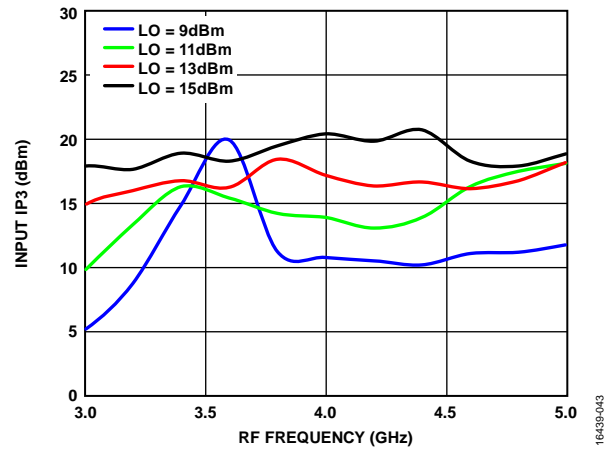


Figure 41. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

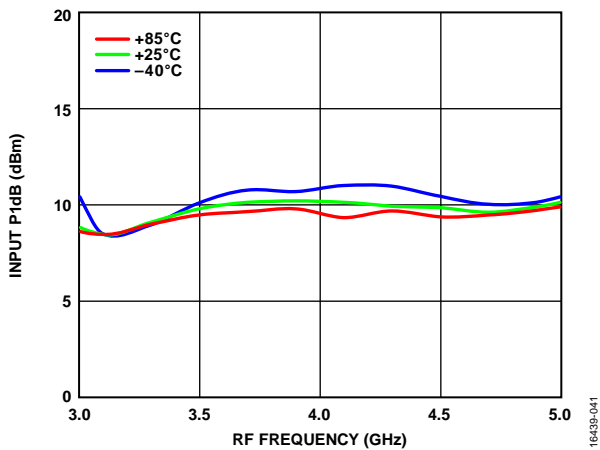


Figure 39. Input P1dB vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

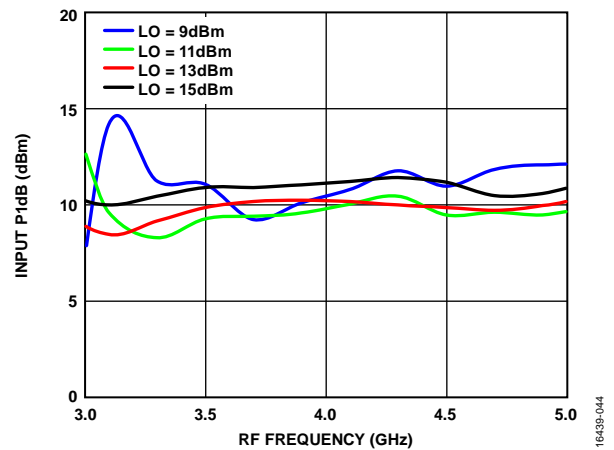


Figure 42. Input P1dB vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

$IF_{IN} = 1500 \text{ MHz, Lower Sideband}$

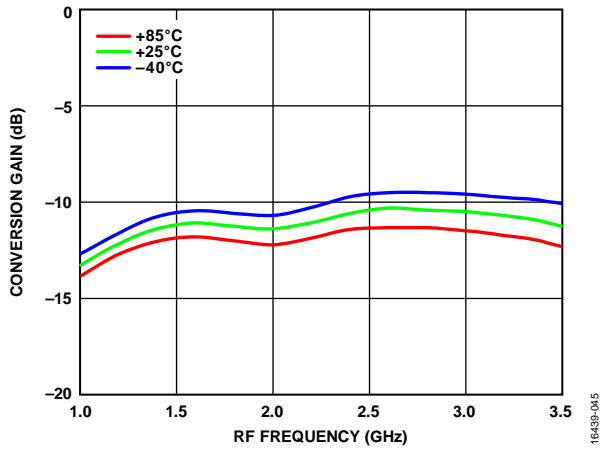


Figure 43. Conversion Gain vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

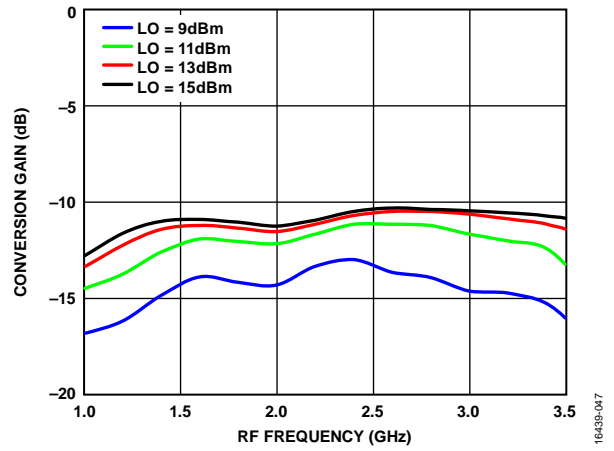


Figure 45. Conversion Gain vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

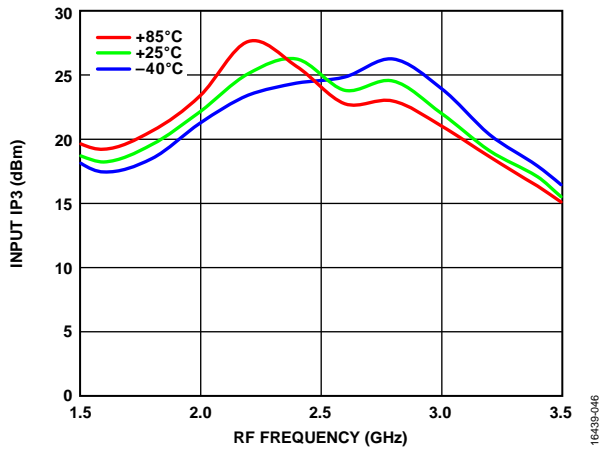


Figure 44. Input IP3 vs. RF Frequency at Various Temperatures, $LO = 13 \text{ dBm}$

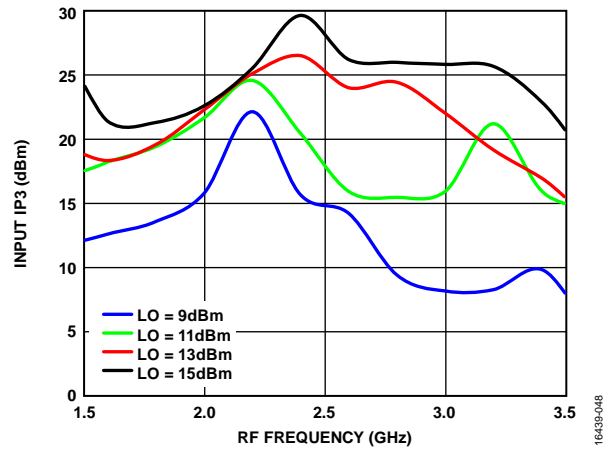


Figure 46. Input IP3 vs. RF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

ISOLATION AND RETURN LOSS

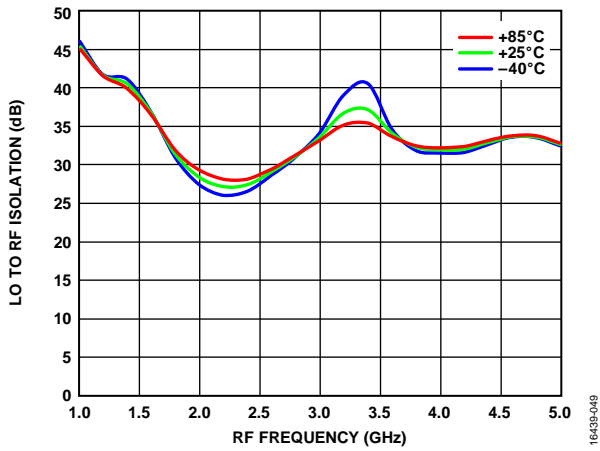


Figure 47. LO to RF Isolation vs. RF Frequency at Various Temperatures, LO = 13 dBm

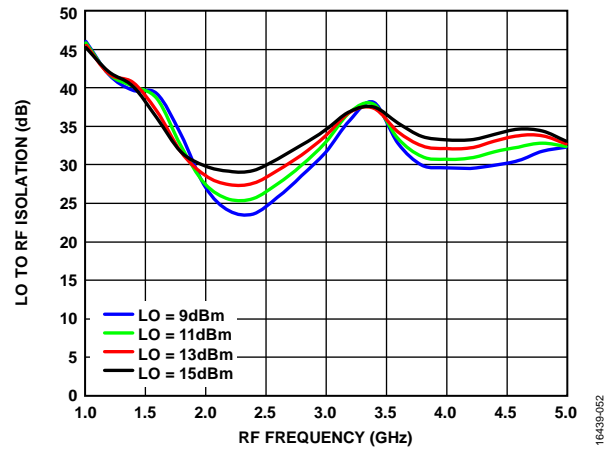


Figure 50. LO to RF Isolation vs. RF Frequency at Various LO Power Levels, TA = 25°C

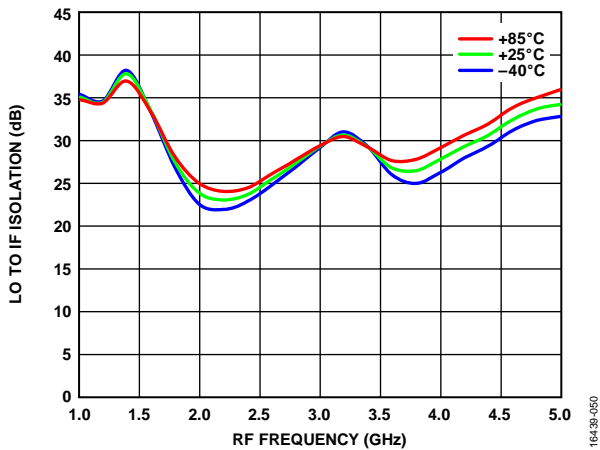


Figure 48. LO to IF Isolation vs. RF Frequency at Various Temperatures, LO = 13 dBm

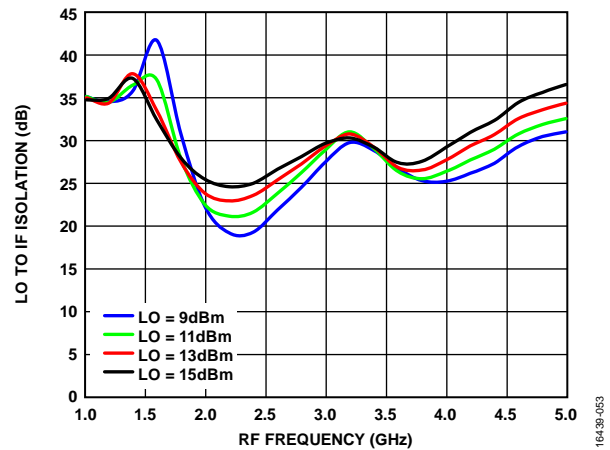


Figure 51. LO to IF Isolation vs. RF Frequency at Various LO Power Levels, TA = 25°C

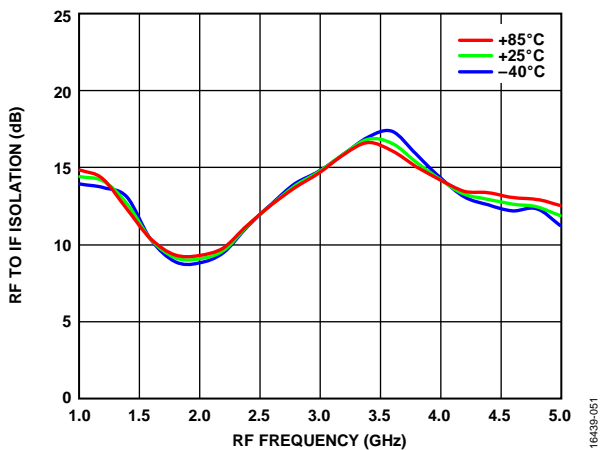


Figure 49. RF to IF Isolation vs. RF Frequency at Various Temperatures, LO = 13 dBm

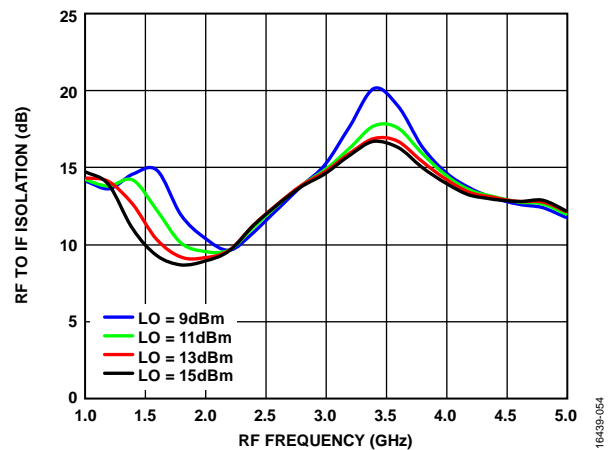


Figure 52. RF to IF Isolation vs. RF Frequency at Various LO Power Levels, TA = 25°C

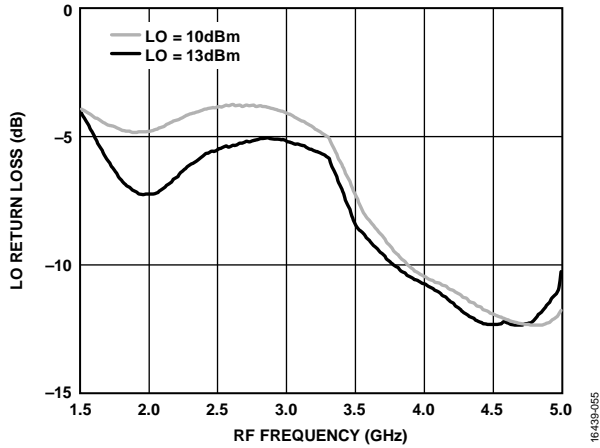


Figure 53. LO Return Loss vs. RF Frequency, $T_A = 25^\circ\text{C}$, LO = 10 dBm and 13 dBm

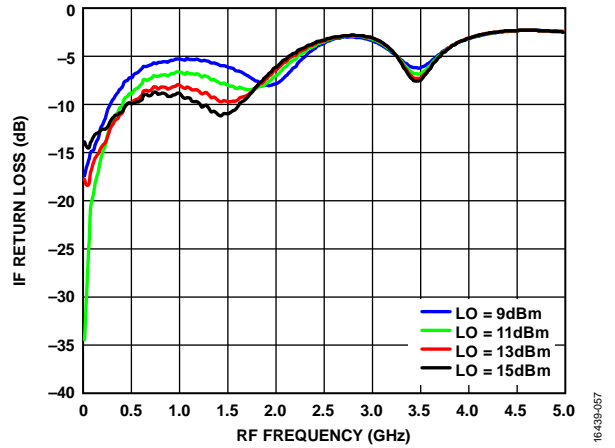


Figure 55. IF Return Loss vs. RF Frequency at Various LO Power Levels, LO at 2.5 GHz, $T_A = 25^\circ\text{C}$

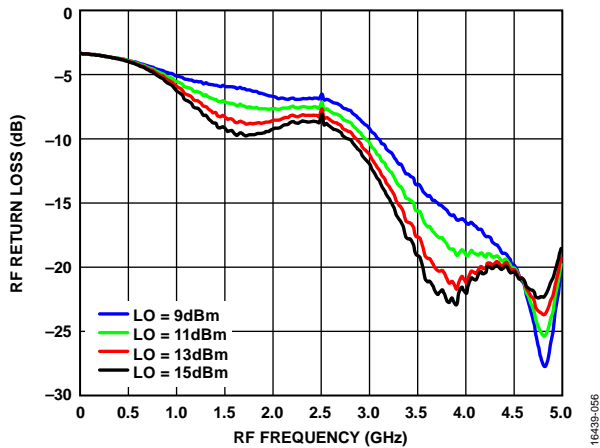


Figure 54. RF Return Loss vs. RF Frequency at Various LO Power Levels, LO at 2.5 GHz, $T_A = 25^\circ\text{C}$

IF BANDWIDTH—DOWNCONVERTER

LO = 1.8 GHz

Upper sideband (low-side LO).

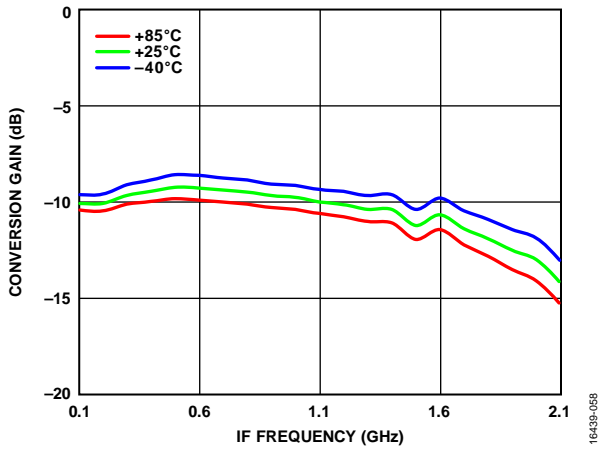


Figure 56. Conversion Gain vs. IF Frequency at Various Temperatures, LO = 13 dBm

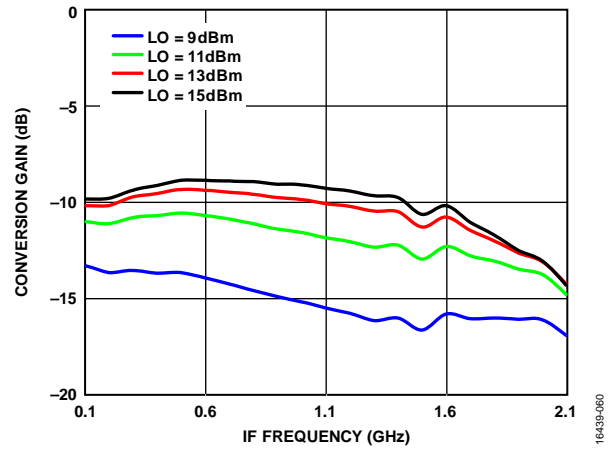


Figure 58. Conversion Gain vs. IF Frequency at Various LO Power Levels, TA = 25°C

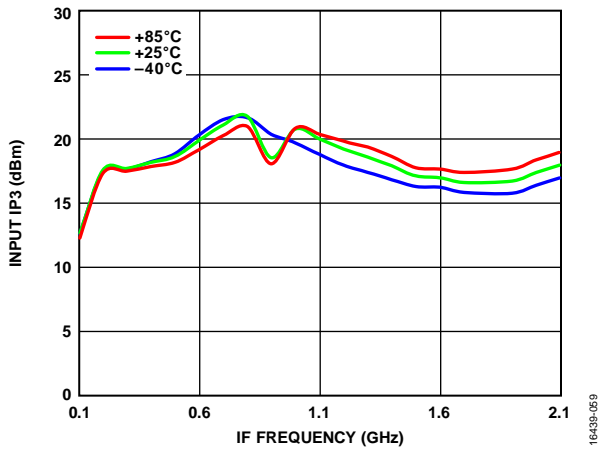


Figure 57. Input IP3 vs. IF Frequency at Various Temperatures, LO = 13 dBm

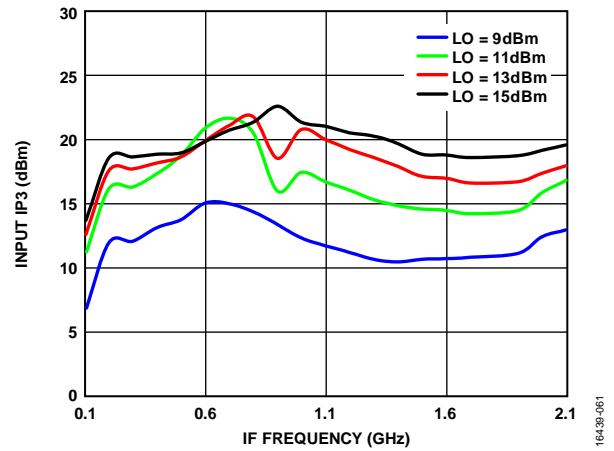


Figure 59. Input IP3 vs. IF Frequency at Various LO Power Levels, TA = 25°C

LO = 4.4 GHz

Lower sideband (high-side LO).

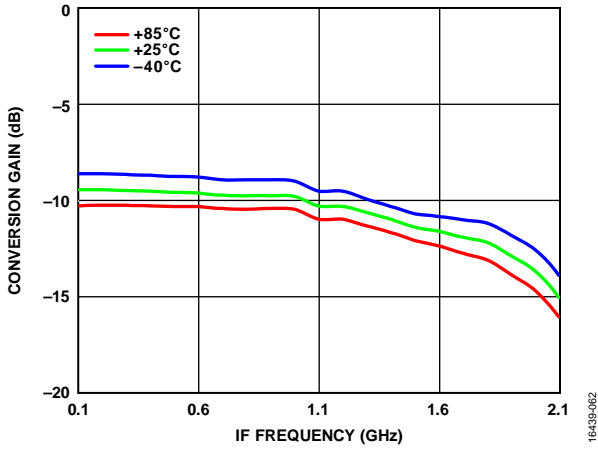


Figure 60. Conversion Gain vs. IF Frequency at Various Temperatures, LO = 13 dBm

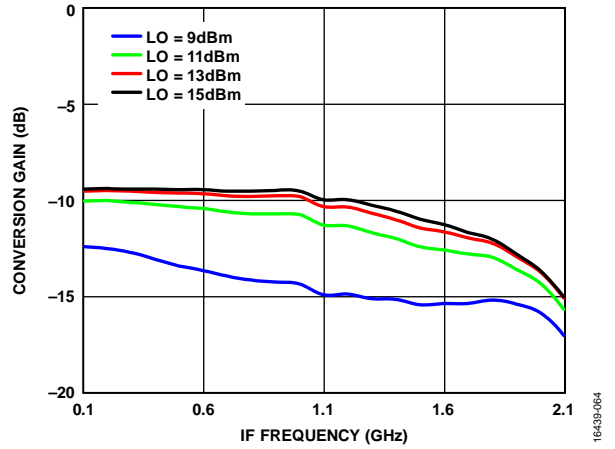


Figure 62. Conversion Gain vs. IF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

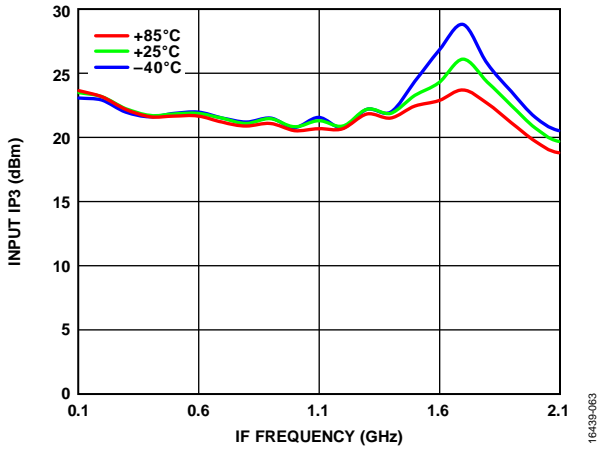


Figure 61. Input IP3 vs. IF Frequency at Various Temperatures, LO = 13 dBm

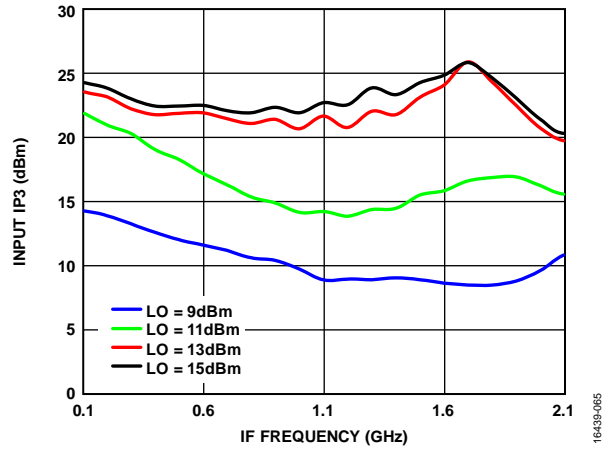


Figure 63. Input IP3 vs. IF Frequency at Various LO Power Levels, $T_A = 25^\circ\text{C}$

SPURIOUS AND HARMONICS PERFORMANCE

Mixer spurious products are measured in dBc from either the RF pin or the IF pin output power level. N/A means not applicable.

LO Harmonics

LO = 13 dBm, and all values in dBc below input LO level and measured at RF port. N/A means not applicable.

Table 5. LO Harmonics at RF

| LO Frequency (GHz) | N × LO Spur at RF Port (dBc) | | | |
|--------------------|------------------------------|----|----|----|
| | 1 | 2 | 3 | 4 |
| 1.5 | 37 | 41 | 57 | 77 |
| 2.0 | 28 | 27 | 49 | 60 |
| 2.5 | 29 | 26 | 45 | 51 |
| 3.0 | 31 | 31 | 35 | 49 |
| 3.5 | 32 | 38 | 50 | 48 |
| 4.0 | 31 | 37 | 39 | 63 |
| 4.5 | 34 | 36 | 40 | 58 |
| 5.0 | 34 | 40 | 46 | 59 |

Downconverter M × N Spurious Outputs

Spur values are (M × RF) – (N × LO).

RF = 3.5 GHz at –10 dBm, LO = 3.6 GHz at 13 dBm.

| | | N × LO | | | | |
|--------|---|--------|-----|-----|-----|-----|
| | | 0 | 1 | 2 | 3 | 4 |
| M × RF | 0 | N/A | –6 | +5 | +17 | +25 |
| | 1 | +6 | 0 | +29 | +37 | +42 |
| | 2 | +63 | +55 | +55 | +55 | +66 |
| | 3 | +80 | +78 | +77 | +83 | +79 |
| | 4 | +77 | +79 | +79 | +82 | +86 |

Upconverter M × N Spurious Outputs

Spur values are (M × IF_{IN}) + (N × LO).

IF_{IN} = 100 MHz at –10 dBm, LO = 3.6 GHz at 13 dBm.

| | | N × LO | | | | |
|--------|----|--------|----|----|----|----|
| | | 0 | 1 | 2 | 3 | 4 |
| M × IF | –4 | 88 | 84 | 82 | 81 | 77 |
| | –3 | 89 | 73 | 79 | 79 | 78 |
| | –2 | 77 | 51 | 59 | 64 | 59 |
| | –1 | 38 | 0 | 42 | 37 | 40 |
| | 0 | N/A | 0 | 8 | 20 | 19 |
| | +1 | 38 | 0 | 44 | 36 | 40 |
| | +2 | 76 | 51 | 61 | 64 | 60 |
| | +3 | 90 | 66 | 79 | 79 | 79 |
| | +4 | 89 | 81 | 79 | 80 | 79 |

THEORY OF OPERATION

The HMC213BMS8E is an ultraminiature, double balanced mixer that can be used as an upconverter or a downconverter from 1.5 GHz to 4.5 GHz.

When used as a downconverter, the HMC213BMS8E downconverts RF values between 1.5 GHz and 4.5 GHz to IF values between dc and 1.5 GHz.

When used as an upconverter, the mixer upconverts IF values between dc and 1.5 GHz to RF between 1.5 GHz and 4.5 GHz

APPLICATIONS INFORMATION

TYPICAL APPLICATION CIRCUIT

Figure 64 shows the typical application circuit for the HMC213BMS8E. The HMC213BMS8E is a passive device and does not require any external components. The LO and RF pins are internally ac-coupled. The IF pin is internally dc-coupled. When IF operation to dc is not required, use of an external series capacitor of a value chosen to pass the necessary IF frequency range is recommended. When IF operation to dc is required, do not exceed the IF source and sink current rating specified in the Absolute Maximum Ratings section.

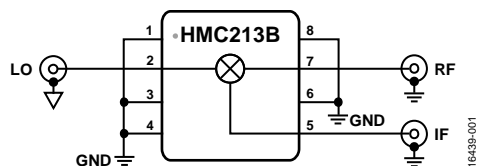


Figure 64. Typical Application Circuit

EVALUATION PCB INFORMATION

Use RF circuit design techniques for the PCB. Ensure that signal lines have 50 Ω impedance. Connect the package ground leads directly to the ground plane (see Figure 65). Use a sufficient number of via holes to connect the top and bottom ground planes. The evaluation circuit board shown in Figure 65 is available from Analog Devices, Inc., upon request.

Table 6. Bill of Materials

| Item | Description |
|------------------|--|
| J1, J2, J3 | PCB mount SMA RF connectors |
| U1 | HMC213BMS8E |
| PCB ¹ | 101650-6 evaluation board on Rogers 4350 |

¹ 101650-6 is the raw bare PCB identifier. Reference EV1HMC213BMS8 when ordering the complete evaluation PCB.

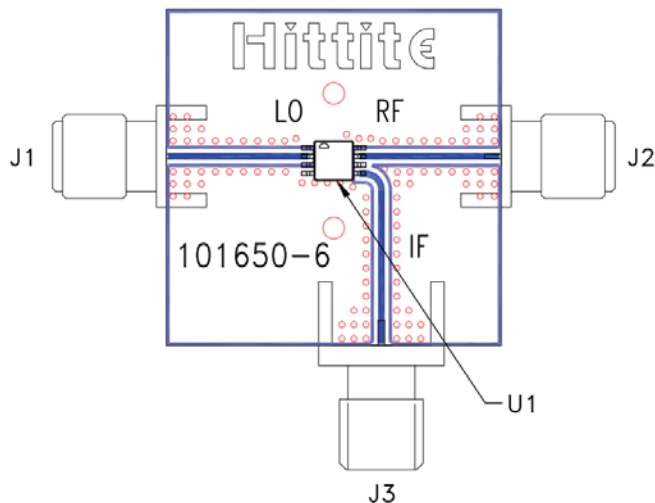
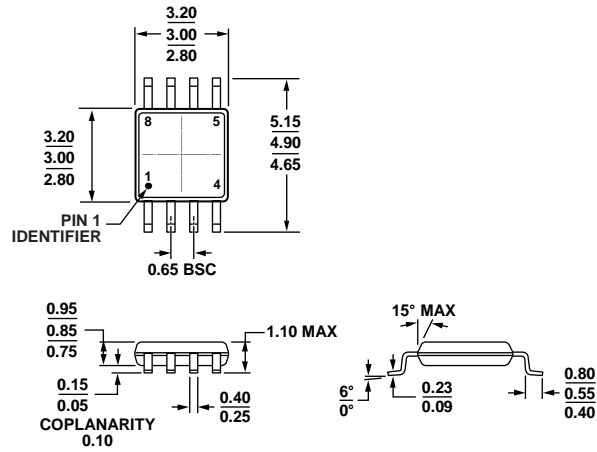


Figure 65. Evaluation PCB Top Layer

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 66. 8-Lead Mini Small Outline Package [MSOP] (RM-8)

Dimensions shown in millimeters

16-07-2008-B

ORDERING GUIDE

| Model ¹ | Temperature Range | Moisture Sensitivity Level (MSL) Rating | Package Description | Package Option |
|--------------------|-------------------|---|--|----------------|
| HMC213BMS8E | -40°C to +85°C | MSL1 | 8-Lead Mini Small Outline Package [MSOP] | RM-8 |
| HMC213BMS8ETR | -40°C to +85°C | MSL1 | 8-Lead Mini Small Outline Package [MSOP] | RM-8 |
| EV1HMC213BMS8 | | | Evaluation PCB | |

¹ The HMC213BMS8E and HMC213BMS8ETR are RoHS compliant parts.

¹ The peak reflow temperature is 260°C. See Table 2 in the Absolute Maximum Ratings section.